ERRATA

Quenched Exponential Decay. E. J. ROBINSON [Phys. Rev. Lett. **57**, 1281 (1986)].

In a Letter on the decay of a bound system into two sequential continua (there has also been analysis of more than two continua[1]), I noted that under suitable conditions, there could be a reduction of the overall decay rate from the value it would have in the absence of the second continuum. This quenching effect had been anticipated in an earlier paper by Druger,[2] a publication that had escaped my notice, and that I wish to acknowledge now.

There is, however, an important difference between Druger's result and mine. He found that quenching invariably occurs, whereas I concluded that the second continuum could either enhance or reduce the decay rate according to whether principal-value or resonant contributions to certain integrals were dominant. (The former normally are more important.) Druger neglected the principal-value terms, which accounts for the disagreement.

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[1]Z. Deng and J. H. Eberly, Phys. Rev. Lett. **58**, 618 (1987).
[2]S. D. Druger, J. Chem. Phys. **73**, 2287 (1980).

Comparison of Dipole Layers, Band Offsets, and Formation Enthalpies of GaAs-AlAs (110) and (001) Interfaces. D. M. BYLANDER and LEONARD KLEINMAN [Phys. Rev. Lett. **59**, 2091 (1987)].

The page number in Ref. 6 is incorrectly given; it should be 3229.

Because in Ref. 6 we found essentially no difference in cohesive energies calculated with twelve- and eighteen-point samples of the (001) Brillouin zone, we mistakenly assumed that the denser sampling we used in the three-layer (110) Brillouin zone would cause no further convergence and we took $3(E_{\rm coh}^{\rm GaAs}+E_{\rm coh}^{\rm AlAs})$ in the (110) and (001) columns of Table I to be identical. We have now recalculated $E_{\rm coh}^{\rm GaAs}$ and $E_{\rm coh}^{\rm AlAs}$ in the three-layer (110) configuration and find them to be larger by 5.55 and 11.02 meV, respectively, making $3(E_{\rm coh}^{\rm GaAs}+E_{\rm coh}^{\rm AlAs})$ larger by 49.71 meV. Thus the formation enthalpy of $(GaAs)_3(AlAs)_3(110)$ becomes 27.8 meV. The monolayer (110) superlattice was recalculated in the three-layer (110) configuration and 16.39 meV more cohesive energy obtained but since 16.57 meV more cohesive energy was obtained for GaAs and AlAs, the formation enthalpy dropped by only 0.2 meV to 14.9 meV. The monolayer (001) and (110) superlattices are identical, differing by a 90° rotation only. The 0.2-meV discrepancy in their calculated formation enthalpies is an indication of the remarkable accuracy of these calculations when we do not make foolish assumptions. We note now that when one goes from the monolayer to three-layer superlattices, the enthalpy per unit cell decreases for (001) but increases for (110) although the enthalpy per atom decreases in all cases.

Capacitance Oscillations in One-Dimensional Electron Systems. T. P. SMITH, III, H. ARNOT, J. M. HONG, C. M. KNOEDLER, S. E. LAUX, and H. SCHMID [Phys. Rev. Lett. **59**, 2802 (1987)].

The first entry in the second column of Table I should be 0.090, not 0.90.

Search for Short-Lived Neutral Particles Emitted in K^+ Decay. N. J. BAKER, H. A. GORDON, D. M. LAZARUS, V. A. POLYCHRONAKOS, P. REHAK, M. J. TANNENBAUM, J. EGGER, W. D. HEROLD, H. KASPAR, V. CHALOUPKA, E. A. JAGEL, H. J. LUBATTI, C. ALLIEGRO, C. CAMPAGNARI, P. S. COOPER, N. J. HADLEY, A. M. LEE, and M. E. ZELLER [Phys. Rev. Lett. **59**, 2832 (1987)].

The thirteenth line of the text should read "sensitive to A^0 lifetimes less than 10^{-12} sec . . . ."